

# FDC6323L Integrated Load Switch

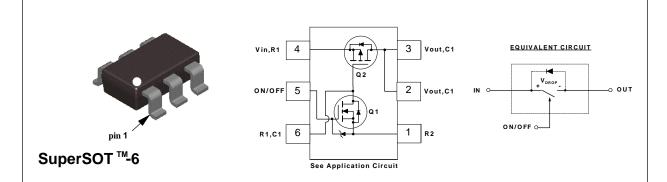
## **General Description**

These Integrated Load Switches are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage high side load switch application where low conduction loss and ease of driving are needed.

#### **Features**

- High density cell design for extremely low on-resistance.
- V<sub>ON/OFF</sub> Zener protection for ESD ruggedness.
   >6KV Human Body Model.
- SuperSOT<sup>TM</sup>-6 package design using copper lead frame for superior thermal and electrical capabilities.





Absolute Maximum Ratings T = 25°C unless otherwise noted

Symbol	Parameter	FDC6323L	Units
V <sub>IN</sub>	Input Voltage Range	3-8	V
V <sub>ON/OFF</sub>	On/Off Voltage Range	1.5 - 8	V
I <sub>L</sub>	Load Current @ V <sub>DROP</sub> =0.5V - Continuous (Note 1)	1.5	A
	- Pulsed (Note 1 & 3)	2.5	
$P_{D}$	Maximum Power Dissipation (Note 2a)	0.7	W
$T_J$ , $T_{STG}$	Operating and Storage Temperature Range	-55 to 150	°C
ESD	Electrostatic Discharge Rating MIL-STD-883D Human Body Model (100pf/1500Ohm)	6	kV
THERMA	L CHARACTERISTICS		•
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 2a)	180	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 2)	60	°C/W

Symbol	Parameter	Conditions	Min	Тур	Max	Units
OFF CHA	RACTERISTICS					•
I <sub>FL</sub>	Forward Leakage Current	V <sub>IN</sub> = 8 V, V <sub>ON/OFF</sub> = 0 V			1	μΑ
I <sub>RL</sub>	Reverse Leakage Current	$V_{IN} = -8 \text{ V}, V_{ON/OFF} = 0 \text{ V}$			-1	μΑ
ON CHAR	ACTERISTICS (Note 3)					
V <sub>IN</sub>	Input Voltage		3		8	V
V <sub>ON/OFF</sub>	On/Off Voltage		1.5		8	V
$V_{DROP}$	Conduction Voltage Drop @ 1A	$V_{IN} = 5 \text{ V}, \ V_{ON/OFF} = 3.3 \text{ V}$		0.145	0.2	V
		$V_{IN} = 3.3 \text{ V}, \ V_{ON/OFF} = 3.3 \text{ V}$		0.178	0.3	
I <sub>L</sub>	Load Current	$V_{DROP} = 0.2 \text{ V}, V_{IN} = 5 \text{ V}, V_{ON/OFF} = 3.3 \text{ V}$	1			Α
		$V_{DROP} = 0.3 \text{ V}, V_{IN} = 3.3 \text{ V}, V_{ONOFF} = 3.3 \text{ V}$	1			

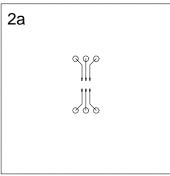
1.  $V_{IN}$ =8V,  $V_{ON/OFF}$ =8V,  $V_{DROP}$ =0.5V,  $T_A$ =25°C

2.  $R_{g,k}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{g,k}$  is guaranteed by design while  $\boldsymbol{R}_{\text{\tiny BCA}}$  is determined by the user's board design.

$$P_D(t) = \frac{T_J - T_A}{R_{BJ,A}(t)} = \frac{T_J - T_A}{R_{BJ,C} + R_{BCA}(t)} = I_D^2(t) \times R_{DS(ON)@T}$$

 $P_D(t) = rac{T_J - T_A}{R_{0J}A(t)} = rac{T_J - T_A}{R_{0J}c^2 + R_{0CA}(t)} = I_D^2(t) \times R_{DS(ON)@T_J}$ Typical R<sub>B,A</sub> for single device operation using the board layouts shown below on FR-4 PCB in a still air environment:

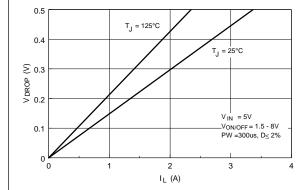
a. 180°C/W when mounted on a 2oz minimum copper pad.



Scale 1 : 1 on letter size paper

3. Pulse Test: Pulse Width  $\leq 300 \mu s,$  Duty Cycle  $\leq 2.0\%$ 

# Typical Electrical Characteristics ( $T_A = 25$ $^{\circ}C$ unless otherwise noted )



0.5
0.4

T<sub>J</sub> = 125°C

T<sub>J</sub> = 25°C

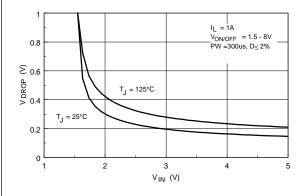
T<sub>J</sub> = 25°C

V<sub>IN</sub> = 3.3V
V<sub>ON/OFF</sub> = 1.5 · 8V
PW = 300us, D<sub>S</sub> 2%

I<sub>L</sub> (A)

Figure 1.  $V_{DROP}$  Versus  $I_L$  at  $V_{IN} = 5V$ .

Figure 2.  $V_{DROP}$  Versus  $I_L$  at  $V_{IN} = 3.3V$ .



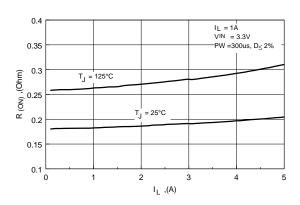


Figure 3.  $V_{DROP}$  Versus  $V_{IN}$  at  $I_L = 1A$ .

Figure 4.  $R_{\text{(ON)}}$  Versus  $I_{\text{L}}$  at  $V_{\text{IN}} = 3.3V$ .

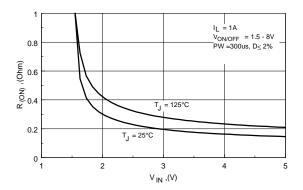
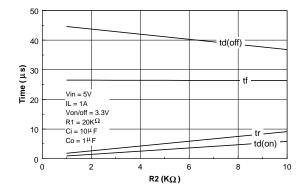


Figure 5. On Resistance Variation with Input Voltage.

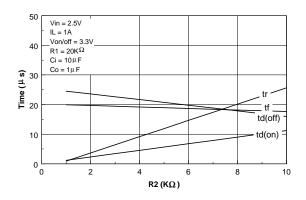
# Typical Electrical Characteristics ( $T_A = 25$ °C unless otherwise noted )



Vin = 3.3V IL = 1A Von/off = 3.3V R1 = 20KΩ Ci = 10μ Ci = 10μ

Figure 6. Switching Variation with R2 at Vin = 5V and R1 = 20K0hm.

Figure 7. Switching Variation with R2 at Vin = 3.3V and R1 = 20KOhm.



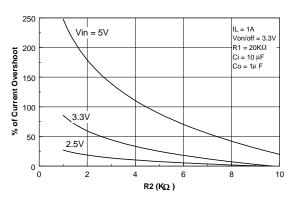
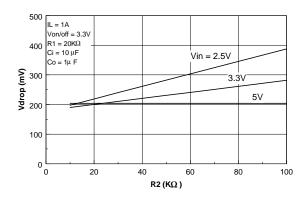


Figure 8. Switching Variation with R2 at Vin = 2.5V and R1 = 20KOhm.

Figure 9. % of Current Overshoot Variation with Vin and R2.



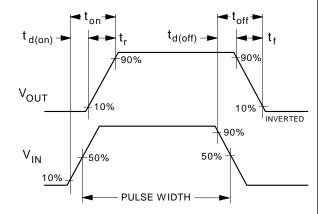


Figure 10. Vdrop Variation with Vin and R2.

Figure 11. Switching Waveforms.

# Typical Electrical Characteristics ( $T_A = 25$ $^{\circ}C$ unless otherwise noted )

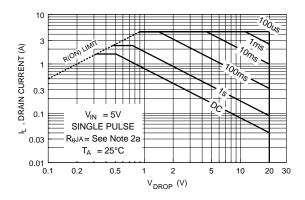


Figure 12. Safe Operating Area.

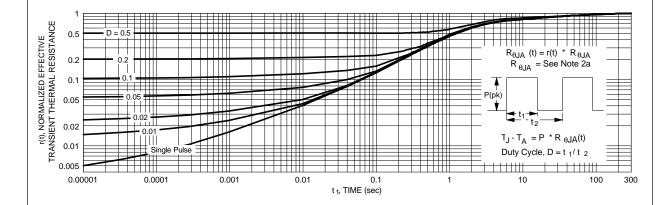
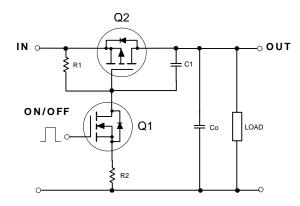


Figure 13. Transient Thermal Response Curve.

Note: Thermal characterization performed on the conditions described in Note 2a. Transient thermal response will change depends on the circuit board design.

# FDC6323L Load Switch Application

## **APPLICATION CIRCUIT**



## **General Description**

This device is particularly suited for compact computer peripheral switching applications where 8V input and 1A output current capability are needed. This load switch integrates a small N-Channel Power MOSFET (Q1) which drives a large P-Channel Power MOSFET (Q2) in one tiny SuperSOT<sup>TM</sup>-6 package.

A load switch is usually configured for high side switching so that the load can be isolated from the active power source. A P-Channel Power MOSFET, because it does not require its drive voltage above the input voltage, is usually more cost effective than using an N-Channel device in this particular application. A large P-Channel Power MOSFET minimizes voltage drop. By using a small N-Channel device the driving stage is simplified.

# **Component Values**

R1 Typical  $10k - 1M\Omega$ 

R2 Typical 0 - 100kΩ (optional) C1 Typical 1000pF (optional)

## **Design Notes**

- R1 is needed to turn off Q2.
- R2 can be used to soft start the switch in case the output capacitance Co is small.
- R2 should be at least 10 times smaller than R1 to guarantee Q1 turns on.
- By using R1 and R2 a certain amount of current is lost from the input. This bias current loss is given by the equation

 $I_{BIAS\_LOSS} = \frac{Vin}{R1 + R2}$ 

when the switch is ON.  $I_{\text{BIAS\_LOSS}}$  can be minimized by selecting a large

value for R1.

R2 and C<sub>RSS</sub> of Q2 make ramp for slow turn on. If excessive overshoot current occurs due to fast turn on, additional capacitance C1 can be added externally to slow down the turn on.

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